# **BGU6102**

# Wideband silicon low-noise amplifier MMIC

Rev. 1 — 21 September 2011

Preliminary data sheet

### 1. Product profile

#### 1.1 General description

The BGU6102 MMIC is a wideband amplifier in Silicon technology for high speed, low-noise applications in a plastic, leadless 6 pin, small outline SOT1209 package.

#### 1.2 Features and benefits

- Small 6-pin leadless package 1.3 mm × 2.0 mm × 0.35 mm
- Low noise high gain microwave MMIC
- Applicable between 40 MHz and 4 GHz
- Supply voltage 1.5 V to 5 V
- Integrated temperature stabilized bias for easy design
- Bias current configurable with external resistor
- 37 GHz transit frequency Silicon technology
- Power-down mode current consumption < 6 μA</p>
- ESD protection on all pins

### 1.3 Applications

- FM radio
- Mobile TV, CMMB
- ISM
- Wireless security

- RKE, TPMS
- AMR, ZigBee, Bluetooth
- WiFi, WLAN, WiMAX
- Low current applications

#### 1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3.0 V;  $V_{ENABLE} \ge$  1.2 V; f = 100 MHz unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ s_{21} ^2$	insertion power gain	[1]	-	13	-	dB
MSG	maximum stable gain	[2]	-	31	-	dB
$NF_{min}$	minimum noise figure	[2]	-	0.7	-	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	[1]	-	-23	-	dBm
IP3 <sub>I</sub>	input third-order intercept point	[1]	-	-15	-	dBm

<sup>[1]</sup> Measurements done on high-ohmic FM radio application board see Section 10.1; I<sub>CC(tot)</sub> = 3.1 mA.

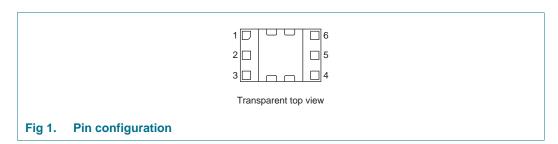


<sup>[2]</sup> Measurements done on characterization board without matching, de-embedded up to the pins;  $I_{CC(tot)} = 3 \text{ mA}$ .

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# 2. Pinning information

### 2.1 Pinning



# 2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$V_{CC}$	1	supply current
n.c.	2	not connected
RF_IN	3	RF in
RF_OUT	4	RF out
ENABLE	5	enable control
CUR_ADJ	6	current adjust
GND	GND	ground pad; RF and DC ground

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BGU6102	XSON7	plastic extremely thin small outline package; no leads; 6 terminals; body $1.3 \times 2.0 \times 0.35$ mm	SOT1209

# 4. Marking

Table 4. Marking

Type number	Marking	Description			
BGU6102	1B*	* = p : made in Hong Kong			
		* = t : made in Malaysia			
* = W : r		* = W : made in China			

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# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled	-	5.5	V
$I_{CC(tot)}$	total supply current	$V_{CC} = 5.0 \text{ V}$	-	40	mΑ
T <sub>stg</sub>	storage temperature		-55	+150	°C
Tj	junction temperature		-	150	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E			
		all pins	-	2000	V
		pin 3	-	3000	V
		Charged Device Model (CDM); According JEDEC standard 22-C101B	-	500	V

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		110	K/W

# 7. Static characteristics

Table 7. Static characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		1.5	-	5.0	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor	[1]	2.1	-	21	mΑ
		$V_{\text{ENABLE}} \leq 0.4 \text{ V}$	[1]	-	-	0.01	mΑ
T <sub>amb</sub>	ambient temperature			-40	+25	+85	°C

<sup>[1]</sup>  $I_{CC(tot)} = I_{CC} + I_{RF\_OUT} + I_{R\_BIAS}$ .

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# 8. Dynamic characteristics

Table 8. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
100 MHz	frequency					
$ s_{21} ^2$	insertion power gain	f = 100 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	16.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	19.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	14.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	28.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	31.5	-	dB
MSG	maximum stable gain	f = 100 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	29.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	31.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	33.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	35.5	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	37.5	-	dB
$NF_{min}$	minimum noise figure	f = 100 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	0.7	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.0	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	f = 100 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-6.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-4.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	4.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	9.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 100 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	3.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	10.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	14.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	19.0	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
150 MHz	frequency					
$ s_{21} ^2$	insertion power gain	f = 150 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	16.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	19.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	24.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	27.5	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	31.0	-	dB
MSG	maximum stable gain	f = 150 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	27.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	29.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	32.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	34.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	36.0	-	dB
$NF_{min}$	minimum noise figure	f = 150 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	0.7	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	0.8	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.0	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 150 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-6.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-4.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	3.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	9.0	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 150 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-0.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	3.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	10.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	14.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	19.0	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
450 MHz	frequency					
$ s_{21} ^2$	insertion power gain	f = 450 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	15.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	18.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	23.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	26.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	29.0	-	dB
MSG	maximum stable gain	f = 450 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	22.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	24.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	27.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	29.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	31.0	-	dB
$NF_{min}$	minimum noise figure	f = 450 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	0.7	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.0	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 450 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.0	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	-0.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	3.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	9.0	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 450 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	4.0	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	10.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	14.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	19.5	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
900 MHz	frequency					
$ s_{21} ^2$	insertion power gain	f = 900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	14.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	16.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	20.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	23.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	25.0	-	dB
MSG	maximum stable gain	f = 900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	19.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	21.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	24.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	26.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	28.0	-	dB
$NF_{min}$	minimum noise figure	f = 900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.7	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	8.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.0	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	-0.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	3.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	10.0	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	1.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	5.0	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	11.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	15.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	20.5	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
1500 MH	z frequency					
$ s_{21} ^2$	insertion power gain	f = 1500 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	11.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	14.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	17.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	19.5	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	21.0	-	dB
MSG	maximum stable gain	f = 1500 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	18.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	19.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	22.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	24.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	25.5	-	dB
$NF_{min}$	minimum noise figure	f = 1500 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	1.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	1.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.9	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	0.9	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.0	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	f = 1500 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	4.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	10.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 1500 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	2.0	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	6.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	12.5	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	16.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	22.5	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
1900 MH	z frequency					
$ s_{21} ^2$	insertion power gain	f = 1900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	10.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	12.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	16.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	17.5	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	19.0	-	dB
MSG	maximum stable gain	f = 1900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	17.0	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	18.5	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	21.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	23.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	24.5	-	dB
$NF_{min}$	minimum noise figure	f = 1900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	1.1	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	1.1	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	1.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	1.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.1	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 1900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	4.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	10.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 1900 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	2.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	6.5	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	13.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	17.0	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	22.5	-	dBm

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
2400 MHz frequency						
$ s_{21} ^2$	insertion power gain	f = 2400 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	8.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	11.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	14.0	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	15.5	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	17.0	-	dB
MSG	maximum stable gain	f = 2400 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	16.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	18.0	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	20.5	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	22.0	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	23.0	-	dB
$NF_{min}$	minimum noise figure	f = 2400 MHz	= 2400 MHz			
		$I_{CC(tot)} = 2 \text{ mA}$	-	1.5	-	dB
		$I_{CC(tot)} = 3 \text{ mA}$	-	1.3	-	dB
		$I_{CC(tot)} = 6 \text{ mA}$	-	1.2	-	dB
		$I_{CC(tot)} = 10 \text{ mA}$	-	1.2	-	dB
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.3	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 2400 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.0	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	0.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	4.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	10.5	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 2400 MHz				
		$I_{CC(tot)} = 2 \text{ mA}$	-	2.5	-	dBm
		$I_{CC(tot)} = 3 \text{ mA}$	-	7.0	-	dBm
		$I_{CC(tot)} = 6 \text{ mA}$	-	13.0	-	dBm
		$I_{CC(tot)} = 10 \text{ mA}$	-	17.5	-	dBm
		$I_{CC(tot)} = 20 \text{ mA}$	-	23.0	-	dBm

**BGU6102 NXP Semiconductors** 

#### Wideband silicon low-noise amplifier MMIC

**Dynamic characteristics** ...continued Table 8.

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3.0 V;  $V_{ENABLE} \ge$  1.2 V unless otherwise specified. All measurements done on characterization board without matching, de-embedded up to the pins.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
3500 MHz frequency							
$ s_{21} ^2$	insertion power gain	f = 3500 MHz					
		$I_{CC(tot)} = 2 \text{ mA}$	-	5.5	-	dB	
		$I_{CC(tot)} = 3 \text{ mA}$	-	7.5	-	dB	
		$I_{CC(tot)} = 6 \text{ mA}$	-	10.5	-	dB	
		$I_{CC(tot)} = 10 \text{ mA}$	-	12.0	-	dB	
		$I_{CC(tot)} = 20 \text{ mA}$	-	13.5	-	dB	
MSG	maximum stable gain	f = 3500 MHz					
		$I_{CC(tot)} = 2 \text{ mA}$	-	16.0	-	dB	
		$I_{CC(tot)} = 3 \text{ mA}$	-	17.5	-	dB	
		$I_{CC(tot)} = 6 \text{ mA}$	-	19.0	-	dB	
		$I_{CC(tot)} = 10 \text{ mA}$	-	18.5	-	dB	
		$I_{CC(tot)} = 20 \text{ mA}$	-	18.5	-	dB	
$NF_{min}$	minimum noise figure	f = 3500 MHz					
		$I_{CC(tot)} = 2 \text{ mA}$	-	2.3	-	dB	
		$I_{CC(tot)} = 3 \text{ mA}$	-	2.2	-	dB	
		$I_{CC(tot)} = 6 \text{ mA}$	-	1.9	-	dB	
		$I_{CC(tot)} = 10 \text{ mA}$	-	1.8	-	dB	
		$I_{CC(tot)} = 20 \text{ mA}$	-	1.9	-	dB	
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 3500 MHz					
		$I_{CC(tot)} = 2 \text{ mA}$	-	-7.5	-	dBm	
		$I_{CC(tot)} = 3 \text{ mA}$	-	-5.5	-	dBm	
		$I_{CC(tot)} = 6 \text{ mA}$	-	-0.5	-	dBm	
		$I_{CC(tot)} = 10 \text{ mA}$	-	4.5	-	dBm	
		$I_{CC(tot)} = 20 \text{ mA}$	-	9.5	-	dBm	
IP3 <sub>O</sub>	output third-order intercept point	f = 3500 MHz					
		$I_{CC(tot)} = 2 \text{ mA}$	-	1.0	-	dBm	
		$I_{CC(tot)} = 3 \text{ mA}$	-	5.0	-	dBm	
		$I_{CC(tot)} = 6 \text{ mA}$	-	11.5	-	dBm	
		$I_{CC(tot)} = 10 \text{ mA}$	-	17.0	-	dBm	
		$I_{CC(tot)} = 20 \text{ mA}$	-	23.5	-	dBm	

#### **Enable control** 9.

Table 9. ENABLE (pin 5)  $-40 \, ^{\circ}\text{C} \le T_{amb} \le +85 \, ^{\circ}\text{C}$ 

V <sub>ENABLE</sub> (V)	State
≤ 0.4	OFF
≥ 1.2	ON

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# 10. Application information

Other applications available. Please contact your local sales representative for more information. Application note(s) available on the NXP website.

### 10.1 High-ohmic FM radio characteristics

Table 10. AC characteristics[1]

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3.0 V;  $I_{CC(tot)}$  = 3.1 mA; f = 100 MHz; measurements done on high-ohmic FM radio application board.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ s_{21} ^2$	insertion power gain		-	13	-	dB
RLin	input return loss		-	1	-	dB
RLout	output return loss		-	20	-	dB
NF	noise figure	$Z_S = 50 \Omega$	-	1.0	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression		-	-23	-	dBm
IP3 <sub>I</sub>	input third-order intercept point		-	-15	-	dBm

<sup>[1]</sup> See application note AN11091 for details.

#### 10.2 50 ohm FM radio characteristics

Table 11. AC characteristics[1]

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.8 V;  $I_{CC(tot)}$  = 4.3 mA; f = 100 MHz; measurements done on 50  $\Omega$  application board.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ s_{21} ^2$	insertion power gain		-	15	-	dB
RLin	input return loss		-	10	-	dB
RL <sub>out</sub>	output return loss		-	14	-	dB
NF	noise figure	$Z_S = 50 \Omega$	-	1.3	1.8	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression		-	-20	-	dBm
IP3 <sub>I</sub>	input third-order intercept point		-	-12	-	dBm

<sup>[1]</sup> See application note AN11090 for details.

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# 11. Package outline

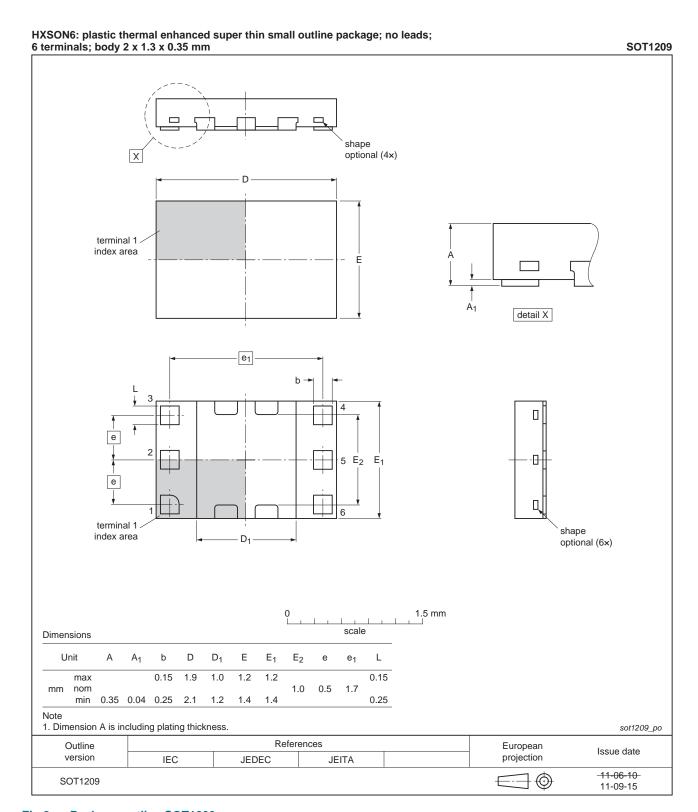


Fig 2. Package outline SOT1209

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# 12. Abbreviations

Table 12. Abbreviations

Acronym	Description
AC	Alternating Current
AMR	Automated Meter Reading
СММВ	China Mobile Multimedia Broadcasting
DC	Direct Current
ESD	ElectroStatic Discharge
FM	Frequency Modulation
GLONASS	GLObal'naya NAvigatsionnaya Sputnikovaya Sistema
GPS	Global Positioning System
НВМ	Human Body Model
ISM	Industrial Scientific Medical
LNA	Low-Noise Amplifier
LNB	Low-Noise Block
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
RF	Radio Frequency
RKE	Remote Keyless Entry
SDARS	Satellite Digital Audio Radio Service
TPMS	Tire-Pressure Monitoring System
UMTS	Universal Mobile Telecommunications System
UWB	Ultra-WideBand
WiMAX	Worldwide Interoperability for Microwave Access
WLAN	Wireless Local Area Network

# 13. Revision history

#### Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU6102 v.1	20110921	Preliminary data sheet	-	-

#### Wideband silicon low-noise amplifier MMIC

# 14. Legal information

#### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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